

AMENDMENTS TO THE SPECIFICATION

Please replace the following paragraphs.

On page 18, in Table 4 beginning on line 13:

[Table 4]

MATERIAL OF LAYER	TEMPERATURE (°C)
p+GaN	950-1025
Mg-DPED p-AlGaN/Mg-DOPED p-GaN SLS	950-1025
<u>AlInGaN/AlInGaN MQW</u> InGaN/AlInGaN MQW	800-900
UNDOPED GaN	800-900
Si-DOPED n-AlGaN Si-DOPED n-GaN SLS	1050-1100
Si-DOPED n-GaN	1050-1100
UNDOPED GaN	1050-1100
BUFFER LAYER	450-600
SiN BUFFER	450-600
SAPPHIRE C-SURFACE SUBSTRATE	